Andrei Vescan

List of Publications by Year
in descending order

176 papers	3,230 citations	147726 31 h-index	197736 49 g-index
176 all docs	176 docs citations	176 times ranked	2861 citing authors

#	Article	IF	Citations
1	12 W/mm AlGaNâ€“GaN HFETs on Silicon Substrates. IEEE Electron Device Letters, 2004, 25, 459-461.	2.2	195
2	Current instabilities in GaN-based devices. IEEE Electron Device Letters, 2001, 22, 62-64.	2.2	142
3	AlGaN/GaN HFETs fabricated on 100-mm GaN on silicon () substrates. Solid-State Electronics, 2002, 46, 1535-1539.	0.8	102
4	Diamond surface-channel FET structure with 200 V breakdown voltage. IEEE Electron Device Letters, 1997, 18, 547-549.	2.2	99
5	Investigation of trapping effects in AlGaN/GaN/Si field-effect transistors by frequency dependent capacitance and conductance analysis. Applied Physics Letters, 2008, 93, 124103.	1.5	95
6	Diamond junction FETs based on Î´-doped channels. Diamond and Related Materials, 1999, 8, 941-945.	1.8	73
7	Heat-spreading diamond films for GaN-based high-power transistor devices. Diamond and Related Materials, 2001, 10, 744-749.	1.8	73
8	Recessed-Gate Enhancement-Mode AlGaN/GaN Heterostructure Field-Effect Transistors on Si with Record DC Performance. Applied Physics Express, 2011, 4, 114102.	1.1	73
9	High temperature, high voltage operation of diamond Schottky diode. Diamond and Related Materials, 1998, 7, 581-584.	1.8	72
10	Very high temperature operation of diamond Schottky diode. IEEE Electron Device Letters, 1997, 18, 556-558.	2.2	67
11	Fabrication of p-channel heterostructure field effect transistors with polarization-induced two-dimensional hole gases at metalâ€“polar GaN/AlInGaN interfaces. Journal Physics D: Applied Physics, 2014, 47, 175103.	1.3	67
12	Study on quaternary AlInGaN/GaN HFETs grown on sapphire substrates. Semiconductor Science and Technology, 2010, 25, 075013.	1.0	62
13	p-Channel Enhancement and Depletion Mode GaN-Based HFETs With Quaternary Backbarriers. IEEE Transactions on Electron Devices, 2013, 60, 3005-3011.	1.6	61
14	The effect of the inversion channel at the AlN/Si interface on the vertical breakdown characteristics of GaN-based devices. Semiconductor Science and Technology, 2014, 29, 115012.	1.0	60
15	Highly Responsive Flexible Photodetectors Based on MOVPE Grown Uniform Few-Layer MoS₂. ACS Photonics, 2020, 7, 1388-1395.	3.2	60
16	Diamond diodes and transistors. Semiconductor Science and Technology, 2003, 18, S59-S66.	1.0	50
17	High-voltage Schottky diode on epitaxial diamond layer. Diamond and Related Materials, 1997, 6, 329-332.	1.8	48
18	Î´-Doping in diamond. Carbon, 1999, 37, 787-791.	5.4	47

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19	High-temperature, high-voltage operation of pulse-doped diamond MESFET. IEEE Electron Device Letters, 1997, 18, 222-224.	2.2	45
20	Chemical Vapor Deposition of Organic-Inorganic Bismuth-Based Perovskite Films for Solar Cell Application. Scientific Reports, 2019, 9, 9774.	1.6	45
21	Small signal and power measurements of AlGaN/GaN HEMT with SiN passivation. Electronics Letters, 2001, 37, 130.	0.5	44
22	Self-Aligned Process for Selectively Etched p-GaN-Gated AlGaN/GaN-on-Si HFETs. IEEE Transactions on Electron Devices, 2018, 65, 3732-3738.	1.6	42
23	The nucleation of highly oriented diamond on silicon via an alternating current substrate bias. Applied Physics Letters, 1996, 68, 3558-3560.	1.5	38
24	characteristics of epitaxial Schottky Au barrier diode on p+ diamond substrate. Diamond and Related Materials, 1995, 4, 661-665.	1.8	37
25	Power Performance at 40 GHz on Quaternary Barrier InAlGaN/GaN HEMT. IEEE Electron Device Letters, 2013, 34, 978-980.	2.2	36
26	Polarization-Engineered Enhancement-Mode High-Electron-Mobility Transistors Using Quaternary AlInGaN Barrier Layers. Journal of Electronic Materials, 2013, 42, 826-832.	1.0	36
27	Scalable Large-Area pâ€“iâ€“n Light-Emitting Diodes Based on WS₂ Monolayers Grown via MOCVD. ACS Photonics, 2019, 6, 1832-1839.	3.2	36
28	First monolithic integration of GaN-based enhancement mode n-channel and p-channel heterostructure field effect transistors. , 2014, , .		35
29	High current p/p/sup +/-diamond Schottky diode. IEEE Electron Device Letters, 1994, 15, 289-291.	2.2	34
30	Demonstration of a GaN-Based Vertical-Channel JFET Fabricated by Selective-Area Regrowth. IEEE Transactions on Electron Devices, 2018, 65, 5329-5336.	1.6	32
31	Flexible Largeâ€Area Lightâ€Emitting Devices Based on WS₂ Monolayers. Advanced Optical Materials, 2020, 8, 2000694.	3.6	32
32	InAlN/GaN HEMTs on Sapphire Substrate With 2.9-W/mm Output Power Density at 18 GHz. IEEE Electron Device Letters, 2011, 32, 1537-1539.	2.2	31
33	Dielectric function and optical properties of quaternary AlInGaN alloys. Journal of Applied Physics, 2011, 110, .	1.1	31
34	Effect of Different Carbon Doping Techniques on the Dynamic Properties of GaN-on-Si Buffers. IEEE Transactions on Electron Devices, 2017, 64, 991-997.	1.6	31
35	Electrothermal characterization of large-area organic light-emitting diodes employing finite-element simulation. Organic Electronics, 2011, 12, 1399-1405.	1.4	30
36	Large-area MoS 2 deposition via MOVPE. Journal of Crystal Growth, 2017, 464, 100-104.	0.7	30

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37	Investigation of large-area OLED devices with various grid geometries. Organic Electronics, 2013, 14, 2387-2391.	1.4	28
38	Effect of Carbon Doping Level on Static and Dynamic Properties of AlGaN/GaN Heterostructures Grown on Silicon. IEEE Transactions on Electron Devices, 2018, 65, 3192-3198.	1.6	28
39	Analysis of an AlGaN/AlN Super-Lattice Buffer Concept for 650-V Low-Dispersion and High-Reliability GaN HEMTs. IEEE Transactions on Electron Devices, 2020, 67, 1113-1119.	1.6	27
40	Electrical characterisation of diamond resistors etched by RIE. Diamond and Related Materials, 1996, 5, 747-751.	1.8	26
41	First polarization-engineered compressively strained AlInGaN barrier enhancement-mode MISHFET. Semiconductor Science and Technology, 2012, 27, 055004.	1.0	26
42	Metalorganic Vapor-Phase Epitaxy Growth Parameters for Two-Dimensional MoS2. Journal of Electronic Materials, 2018, 47, 910-916.	1.0	25
43	Fusion of intraoperative cone-beam CT and endoscopic video for image-guided procedures. , 2010, , .		24
44	Electrical properties of quasi-vertical Schottky diodes. Semiconductor Science and Technology, 2012, 27, 085015.	1.0	24
45	Threshold Voltage Engineering in GaN-Based HFETs: A Systematic Study With the Threshold Voltage Reaching More Than 2 V. IEEE Transactions on Electron Devices, 2015, 62, 538-545.	1.6	23
46	Improved luminescence properties of MoS₂ monolayers grown via MOCVD: role of pre-treatment and growth parameters. Nanotechnology, 2018, 29, 295704.	1.3	23
47	Application of highly oriented, planar diamond (HOD) films of high mechanical strength in sensor technologies. Diamond and Related Materials, 1998, 7, 779-782.	1.8	22
48	AlGaN/GaN HFETs on 100 mm Silicon Substrates for Commercial Wireless Applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 52-56.	0.8	22
49	AlN barrier HFETs with AlGaN channels to shift the threshold voltage to higher positive values: a proposal. Semiconductor Science and Technology, 2013, 28, 074017.	1.0	22
50	Current limitation after pinch-off in AlGaN/GaN FETs. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 1.	1.0	21
51	Charge balancing in GaN-based 2-D electron gas devices employing an additional 2-D hole gas and its influence on dynamic behaviour of GaN-based heterostructure field effect transistors. Journal of Applied Physics, 2015, 117, .	1.1	21
52	Growth Studies on Quaternary AlInGaN Layers for HEMT Application. Journal of Electronic Materials, 2012, 41, 905-909.	1.0	20
53	Evaluation of interpolations of InN, AlN and GaN lattice and elastic constants for their ternary and quaternary alloys. Journal Physics D: Applied Physics, 2013, 46, 245502.	1.3	19
54	Relaxation and critical strain for maximum In incorporation in AlInGaN on GaN grown by metal organic vapour phase epitaxy. Journal of Applied Physics, 2012, 112, 093524.	1.1	18

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55	Effect of stress voltage on the dynamic buffer response of GaN-on-silicon transistors. Journal of Applied Physics, 2016, 119, .	1.1	17
56	Electrical properties of thermally oxidized AlInN/AlN/GaN-based metal oxide semiconductor hetero field effect transistors. Journal of Applied Physics, 2011, 110, .	1.1	16
57	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. Applied Physics Letters, 2013, 102, .	1.5	16
58	Morphology Control of Organicâ€“Inorganic Bismuthâ€Based Perovskites for Solar Cell Application. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800409.	0.8	16
59	Selectively grown ohmic contacts to -doped diamond films. Electronics Letters, 1996, 32, 1419.	0.5	15
60	AlGaN/GaN MODFETs on semi-insulating SiC with 3 W/mm at 20 GHz. Electronics Letters, 2000, 36, 1234.	0.5	15
61	Interplay between C-doping, threading dislocations, breakdown, and leakage in GaN on Si HEMT structures. AIP Advances, 2020, 10, .	0.6	15
62	The III-Nitride Double Heterostructure Revisited: Benefits for Threshold Voltage Engineering of MIS Devices. IEEE Transactions on Electron Devices, 2016, 63, 606-613.	1.6	14
63	Zeroâ€Bias Powerâ€Detector Circuits based on MoS₂ Fieldâ€Effect Transistors on Waferâ€Scale Flexible Substrates. Advanced Materials, 2022, 34, e2108469.	11.1	14
64	Optimisation of AlInN/GaN HEMT structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2041-2043.	0.8	13
65	Influence of barrier thickness on AlInN/AlN/GaN heterostructures and device properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1041.	0.8	13
66	Influence of mask material and process parameters on etch angle in a chlorine-based GaN dry etch. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	13
67	GaN-on-Si Enhancement Mode Metal Insulator Semiconductor Heterostructure Field Effect Transistor with On-Current of 1.35 A/mm. Japanese Journal of Applied Physics, 2013, 52, 090204.	0.8	13
68	Semi-polar {1â€‰$mathbf{ar{1}}$ â€‰â€‰0â€‰1} blue and green InGaN/GaN light-emitting diodes on micro-stripe patterned Si (1â€‰0â€‰0). Journal Physics D: Applied Physics, 2015, 48, 485103.	1.3	13
69	H2S-free Metal-Organic Vapor Phase Epitaxy of Coalesced 2D WS2 Layers on Sapphire. MRS Advances, 2019, 4, 593-599.	0.5	13
70	Homogeneous lithium fluoride films as a high resolution electron beam resist. Microelectronic Engineering, 1992, 17, 287-290.	1.1	12
71	Actuator - sensor technology on "electronic grade" diamond films. Microsystem Technologies, 1998, 5, 38-43.	1.2	11
72	Effect of Illumination on the Electrical Characteristics of AlGaN/GaN FETs. Physica Status Solidi A, 1999, 176, 209-212.	1.7	11

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73	MOVPE, processing and characterization of AlGaN/GaN HEMTs with different Al concentrations on silicon substrates. Journal of Crystal Growth, 2007, 298, 843-847.	0.7	11
74	Selective MOVPE of InGaN-based LED structures on non-planar Si (111) facets of patterned Si (100) substrates. Journal of Crystal Growth, 2014, 391, 33-40.	0.7	11
75	The controlled growth of GaN microrods on Si(111) substrates by MOCVD. Journal of Crystal Growth, 2015, 414, 200-204.	0.7	11
76	MBE grown AlGaN/GaN MODFETs with high breakdown voltage. Journal of Crystal Growth, 1999, 201-202, 327-331.	0.7	10
77	Characterization of AlGaN/GaN MISHFETs on a Si substrate by static and high-frequency measurements. Semiconductor Science and Technology, 2009, 24, 075014.	1.0	10
78	Quaternary nitride heterostructure field effect transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2001-2003.	0.8	10
79	RF performance of InAlN/AlN/GaN HEMTs on sapphire substrate. Electronics Letters, 2011, 47, 212.	0.5	10
80	Strong charge carrier localization interacting with extensive nonradiative recombination in heteroepitaxially grown m-plane GaInN quantum wells. Semiconductor Science and Technology, 2011, 26, 105017.	1.0	10
81	Investigation of plasma-oxidized aluminium as a gate dielectric for AlGaN/GaN MISHFETs. Semiconductor Science and Technology, 2012, 27, 062001.	1.0	10
82	Quaternary Enhancement-Mode HFET With In Situ SiN Passivation. IEEE Electron Device Letters, 2012, 33, 519-521.	2.2	10
83	First Small-Signal Data of GaN-Based p-Channel Heterostructure Field Effect Transistors. Japanese Journal of Applied Physics, 2013, 52, 128001.	0.8	10
84	Comparison of MOCVD and MBE Regrowth for CAVET Fabrication. Electronics (Switzerland), 2019, 8, 377.	1.8	10
85	Growth and Characterization of Vertical and Lateral pâ€n Junctions Formed by Selectiveâ€Area pâ€GaN MOVPE on Patterned Templates. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800677.	0.8	10
86	MOVPE of Large-Scale MoS2/WS2, WS2/MoS2, WS2/Graphene and MoS2/Graphene 2D-2D Heterostructures for Optoelectronic Applications. MRS Advances, 2020, 5, 1625-1633.	0.5	10
87	Highly rectifying Au-contacts on diamond-on-silicon substrate. IEEE Electron Device Letters, 1996, 17, 270-272.	2.2	9
88	Power handling limits and degradation of large area AlGaN/GaN RF-HEMTs. Solid-State Electronics, 2003, 47, 123-125.	0.8	9
89	In situ SiN passivation of AlInN/GaN heterostructures by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2104-2106.	0.8	9
90	Polarization-reduced quaternary InAlGaN/GaN HFET and MISHFET devices. Semiconductor Science and Technology, 2012, 27, 055012.	1.0	9

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91	Oxygen addition to fluorine based SiN etch process: Impact on the electrical properties of AlGaN/GaN 2DEG and transistor characteristics. Solid-State Electronics, 2012, 67, 90-93.	0.8	9
92	Characterization of GaN-based p-channel device structures at elevated temperatures. Semiconductor Science and Technology, 2014, 29, 075002.	1.0	9
93	Reaction engineering of CVD methylammonium bismuth iodide layers for photovoltaic applications. Journal of Materials Research, 2019, 34, 608-615.	1.2	9
94	On the anisotropic wafer curvature of GaN-based heterostructures on Si(110) substrates grown by MOVPE. Journal of Crystal Growth, 2011, 315, 220-223.	0.7	8
95	Fabrication of Methylammonium Bismuth Iodide Layers Employing Methylamine Vapor Exposure. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900169.	0.8	8
96	Showerhead-assisted chemical vapor deposition of CsPbBr3 films for LED applications. Journal of Materials Research, 2021, 36, 1813-1823.	1.2	8
97	Transfer-free, scalable photodetectors based on MOCVD-grown 2D-heterostructures. 2D Materials, 2021, 8, 045015.	2.0	8
98	General diamond Schottky-barrier diode model from locus diagram analysis. Diamond and Related Materials, 1994, 3, 887-890.	1.8	7
99	Extraction of the active acceptor concentration in (pseudo-) vertical GaN MOSFETs using the body-bias effect. Microelectronics Journal, 2019, 91, 42-45.	1.1	7
100	Study on growth and electrical performance of doubleâ€heterostructure AlGaN/GaN/AlGaN fieldâ€effectâ€transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003.	0.8	6
101	Epitaxy and characterisation of AlInGaN heterostructures for HEMT application. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S470.	0.8	6
102	On the thermal oxidation of AlInN/AlN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2213-2215.	0.8	6
103	Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. Journal of Crystal Growth, 2012, 358, 51-56.	0.7	6
104	Highly nâ€type doped InGaN films for efficient direct solar hydrogen generation. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 964-967.	0.8	6
105	InGaN: Direct correlation of nanoscopic morphology features with optical and structural properties. Applied Physics Letters, 2014, 105, 072108.	1.5	6
106	Investigations of the electrochemical stability of InGaN photoanodes in different electrolytes. Physica Status Solidi (B): Basic Research, 2015, 252, 895-899.	0.7	6
107	Direct Chemical Vapor Phase Deposition of Organometal Halide Perovskite Layers. MRS Advances, 2017, 2, 1189-1194.	0.5	6
108	High-mobility GaN-on-sapphire p-n diodes with near-unity ideality factor and large breakdown voltage. Journal Physics D: Applied Physics, 2019, 52, 285101.	1.3	6

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109	Detailed study on MOCVD of wafer-scale MoS2 monolayers: From nucleation to coalescence. MRS Advances, 2022, 7, 751-756.	0.5	6
110	Performance and limitations of AlGaN/GaN HFETs grown on sapphire and SiC substrates. , 0, , .		5
111	Processing approaches of AlGaN/GaN Metal Insulator Semiconductor Hetero Field Effect Transistors (MISHFET) on Si (111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1033-S1036.	0.8	5
112	Impact of gate dielectric thickness on the electrical properties of AlGaN/GaN MISHFETs on Si(111) substrate. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1342-1344.	0.8	5
113	Irregular spectral position of E || c component of polarized photoluminescence from m-plane InGaN/GaN multiple quantum wells grown on LiAlO2. Applied Physics Letters, 2011, 99, 232114.	1.5	5
114	Formation of a Monocrystalline, M-Plane AlN Layer by the Nitridation of $gamma$-LiAlO$_{2}$(100). Applied Physics Express, 2012, 5, 105501.	1.1	5
115	Quaternary nitride enhancement mode HFET with 260 mS/mm and a threshold voltage of +0.5 V. , 2012, , .		5
116	Characterization of charge injection and photovoltaic effects of hybrid inorganic-organic GaN/pentacene heterostructures. Applied Physics Letters, 2013, 103, .	1.5	5
117	In-situ decomposition and etching of AlN and GaN in the presence of HCl. Journal of Crystal Growth, 2014, 393, 89-92.	0.7	5
118	The effect of AlN nucleation growth conditions on the inversion channel formation at the AlN/silicon interface. , 2015, , .		5
119	Limitations of threshold voltage engineering of AlGaN/GaN heterostructures by dielectric interface charge density and manipulation by oxygen plasma surface treatments. Journal of Applied Physics, 2016, 119, .	1.1	5
120	Evaluation of High-Temperature High-Frequency GaN-Based LC-Oscillator Components. IEEE Transactions on Electron Devices, 2020, 67, 4587-4591.	1.6	5
121	Advanced buffers for AlGaN/GaN HEMT and InGaN/GaN MQW on silicon substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2342-2345.	0.8	4
122	MOVPE growth, optical and electrical characterization of thick Mg-doped InGaN layers. Journal of Crystal Growth, 2013, 370, 2-6.	0.7	4
123	Effect of antimony on growth mode and properties of thick InGaN layers. Journal of Crystal Growth, 2015, 414, 42-48.	0.7	4
124	AlGaN/AlN-GaN-SL HEMTs with Multiple 2DEG Channels. Journal of Electronic Materials, 2015, 44, 1263-1267.	1.0	4
125	Optical and structural properties of GaN epitaxial layers on LiAlO2 substrates and their correlation with basal-plane stacking faults. Journal of Crystal Growth, 2016, 434, 62-66.	0.7	4
126	Fabrication and Characterization of Air-Stable Organic-Inorganic Bismuth-Based Perovskite Solar Cells. MRS Advances, 2018, 3, 3085-3090.	0.5	4

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127	Development of a III-nitride electro-optical modulator for UVâ€“vis. Japanese Journal of Applied Physics, 2019, 58, SCCC04.	0.8	4
128	Optimization of Transparent Organic Light-Emitting Diodes by Simulation-Based Design of Organic Capping Layers. Journal of Nanoscience and Nanotechnology, 2019, 19, 3959-3963.	0.9	4
129	GaN Micropillar Schottky Diodes with High Breakdown Voltage Fabricated by Selectiveâ€Area Growth. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900676.	0.8	4
130	Fabrication of Highly Oriented, Smooth Diamond Films on Silicon for Electronic Devices. Materials Research Society Symposia Proceedings, 1996, 423, 63.	0.1	3
131	First diamond power FET structure. , 1997, , .		3
132	Growth of GaN in a planetary MOCVD hotwall system. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2041-2043.	0.8	3
133	The effect of gate length variation on InAlGaN/GaN HFET device characteristics. Semiconductor Science and Technology, 2012, 27, 035009.	1.0	3
134	HCl-assisted growth of GaN and AlN. Journal of Crystal Growth, 2013, 370, 30-35.	0.7	3
135	Insulating behavior of interfaces in regrown Al0.23Ga0.77N/GaN double heterostructures on Al0.07Ga0.93N back-barrier templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 799-802.	0.8	3
136	Growth properties and electrochemical characterization of InGaN photoanodes with different In concentrations. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 746-749.	0.8	3
137	Low-Temperature Processed Hybrid Organic/Silicon Solar Cells with Power Conversion Efficiency up to 6.5%. Materials Research Society Symposia Proceedings, 2015, 1771, 201-206.	0.1	3
138	Controlling the interface charge density in GaN-based metal-oxide-semiconductor heterostructures by plasma oxidation of metal layers. Journal of Applied Physics, 2015, 117, 214503.	1.1	3
139	Simplified efficient phosphorescent organic light-emitting diodes by organic vapor phase deposition. Applied Physics Letters, 2017, 111, 243301.	1.5	3
140	Investigation of Perovskite Solar Cells Employing Chemical Vapor Deposited Methylammonium Bismuth Iodide Layers. MRS Advances, 2018, 3, 3069-3074.	0.5	3
141	H₂S-free Metal-Organic Vapor Phase Epitaxy of Coalesced 2D WS₂ Layers on Sapphire - ERRATUM. MRS Advances, 2019, 4, e1-e1.	0.5	3
142	High-Intensity CsPbBr3 Perovskite LED using Poly(bis(4-phenyl)(2,4,6-trimethylphenyl)amine) as Hole Transport and Electron-Blocking Layer. MRS Advances, 2020, 5, 411-419.	0.5	3
143	Measurement of stress in a synthetic diamond substrate using the photoelastic method. Diamond and Related Materials, 1996, 5, 664-668.	1.8	2
144	Characteristics of AlGaN/GaN HEMT devices with SiN passivation. , 0, , .		2

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145	AlInN/GaN HEMTs on sapphire: dc and pulsed characterisation. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1926-1928.	0.8	2
146	High-excitation luminescence properties of m-plane GaN grown on LiAlO2 substrates. Journal of Crystal Growth, 2011, 329, 33-38.	0.7	2
147	Characterization of charge carrier injection in organic and hybrid organic/inorganic semiconductor devices by capacitance-voltage measurements. , 2012, , .		2
148	Enhancement mode InAlGaN/GaN MISHFETs with plasma-oxidised AlOx/TiOxas gate insulator. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 840-843.	0.8	2
149	Optimization of hybrid organic/inorganic poly(3-hexylthiophene-2,5-diyl)/silicon solar cells. Journal of Photonics for Energy, 2016, 6, 025504.	0.8	2
150	Limitations for Reliable Operation at Elevated Temperatures of Al 2 O 3 /AlGaN/GaN Metalâ€“Insulatorâ€“Semiconductor Highâ€Electronâ€Mobility Transistors Grown by Metalâ€Organic Chemical Vapor Deposition on Silicon Substrate. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900697.	0.8	2
151	Showerhead-Assisted Chemical Vapor Deposition of Perovskite Films for Solar Cell Application. MRS Advances, 2020, 5, 385-393.	0.5	2
152	‹title›Epitaxial diamond Schottky diode on p+-substrate‹/title›. , 1994, , .		1
153	1000Â°C operation of diamond Schottky diode. , 0, , .		1
154	Devices at High Temperaturesâ€”Status and Prospects. Israel Journal of Chemistry, 1998, 38, 105-112.	1.0	1
155	Processing and characterization of recessed-gate AlGaN/GaN HFETs. , 2008, , .		1
156	Modelling of hole transport in a small-molecule organic material assuming carrier heating in a Gaussian density of states. , 2012, , .		1
157	AlGaN/GaN heterostructure field-effect transistors regrown on nitrogen implanted templates. Semiconductor Science and Technology, 2013, 28, 085006.	1.0	1
158	Improved Light Outcoupling from OLED by Non-Wave-Guiding Anode Designs. Materials Research Society Symposia Proceedings, 2014, 1627, 1.	0.1	1
159	Investigation of organic semiconductor interlayers in hybrid PEDOT:PSS/silicon solar cells. Journal of Photonics for Energy, 2016, 6, 045503.	0.8	1
160	Influence of Band Tailing on Photo- and Electroluminescence Polarization of m-Plane InGaN/GaN Quantum Well Heterostructures. Journal of Applied Spectroscopy, 2016, 82, 956-960.	0.3	1
161	AlGaN/GaN high electron mobility transistor oscillator for high temperature and high frequency. Electronics Letters, 2021, 57, 148-150.	0.5	1
162	Gallium nitride on silicon. , 0, , .		0

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163	Advanced Modeling of MISHFET Devices and their Performance in Current-Mode Class-D Power Amplifiers. , 2008, , .		0
164	Temperatureâ€resolved photoluminescence of nonpolar InGaN/GaN multiple quantum well heterostructures grown on LiAlO₂. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 532-535.	0.8	0
165	Novel GaN-based transistors using polarization engineering. , 2014, , .		0
166	Pentacene/K12 solar cells formed by organic vapor phase deposition. Journal of Photonics for Energy, 2014, 4, 043092.	0.8	0
167	Strain relief mechanisms and growth behavior of superlattice distributed Bragg reflectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 758-761.	0.8	0
168	Advanced thin-film chip concepts for efficient InGaN solar cells. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2053-2058.	0.8	0
169	Transparent Ag-Free OLED Fabricated by OVPD Using Thin Au Contacts. MRS Advances, 2016, 1, 477-482.	0.5	0
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171	Backside Contacting for Uniform Luminance in Large-Area OLED. MRS Advances, 2017, 2, 2275-2280.	0.5	0
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